

MOSFETs Silicon N-Channel MOS (U-MOSIII)

SSM3K77MFV

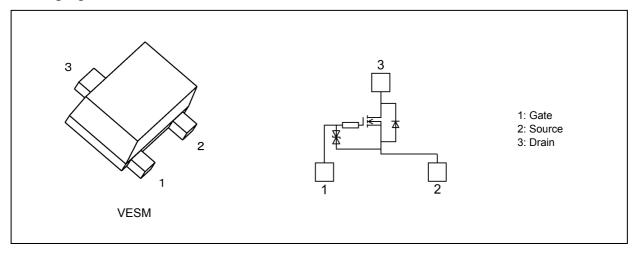
1. Applications

- · High-Speed Switching
- · Analog Switches

2. Features

- (1) 1.5 V gate drive voltage.
- (2) Low drain-source on-resistance
 - $\cdot R_{\rm DS(ON)} = 5.60 \ \Omega \ ({\rm max}) \ (@V_{\rm GS} = 1.5 \ {\rm V}, \ {\rm I_D} = 10 \ {\rm mA})$
 - $\cdot R_{\rm DS(ON)} = 4.05 \ \Omega \ ({\rm max}) \ (@V_{\rm GS} = 1.8 \ {\rm V}, \ {\rm I_D} = 20 \ {\rm mA})$
 - $\cdot R_{\rm DS(ON)} = 3.02 \ \Omega \ ({\rm max}) \ (@V_{\rm GS} = 2.5 \ {\rm V}, \ I_{\rm D} = 50 \ {\rm mA})$
 - \cdot R_{DS(ON)} = 2.20 Ω (max) (@V_{GS} = 4.5 V, I_D = 100 mA)
- (3) Low leakage current

3. Packaging and Internal Circuit



Rev.1.0



4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	20	V
Gate-source voltage		V_{GSS}	±10	
Drain current	(Note 1)	I _D	250	mA
Drain current (pulsed)	(Note 1)	I _{DP}	500	
Power dissipation	(Note 2)	P _D	150	mW
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 0.585 mm²)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, $R_{th(ch-a)}$, and the drain power dissipation, P_D , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 5 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.08	μΑ
			$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_		±1	
Drain cut-off current		I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	_		0.08	
Drain-source breakdown voltage		V _{(BR)DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	20			٧
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	$I_D = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12			
Gate threshold voltage	(Note 2)	V_{th}	$V_{DS} = 3 \text{ V}, I_{D} = 1 \text{ mA}$	0.35		1.0	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	$I_D = 100 \text{ mA}, V_{GS} = 4.5 \text{ V}$	_	1.65	2.20	Ω
			$I_D = 50 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	2.16	3.02	
			$I_D = 20 \text{ mA}, V_{GS} = 1.8 \text{ V}$	_	2.66	4.05	
			I _D = 10 mA, V _{GS} = 1.5 V		3.07	5.60	
Forward transfer admittance	(Note 3)	Y _{fs}	V _{DS} = 3 V, I _D = 100 mA	0.14	0.28	_	S

- Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

 Take this into consideration when using the device.

Note 3: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		12		pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	4.1		
Output capacitance	Coss			5.5		
Switching time (turn-on time)	t _{on}	V_{DD} = 10 V, I_{D} = 100 mA, V_{GS} = 0 to 2.5 V, R_{GS} = 50 Ω		18		ns
Switching time (turn-off time)	t _{off}	Common source, See Chapter 5.3.	_	36	_	

5.3. Switching Time Test Circuit

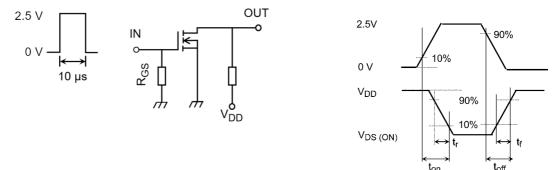


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	$I_D = -250 \text{ mA}, V_{GS} = 0 \text{ V}$		-0.90	-1.2	V

Note 1: Pulse measurement.



6. Marking

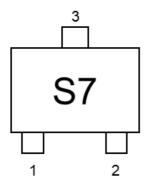


Fig. 6.1 Marking



7. Characteristics Curves (Note)

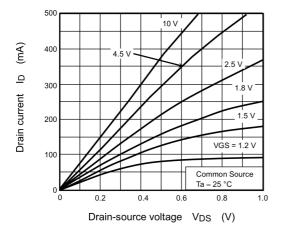
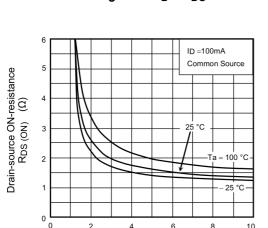


Fig. 7.1 I_D - V_{DS}



Gate-source voltage V_{GS} (V) Fig. 7.3 $R_{DS(ON)}$ - V_{GS}

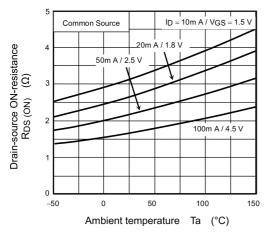


Fig. 7.5 R_{DS(ON)} - T_a

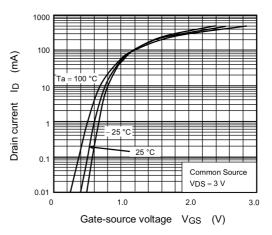


Fig. 7.2 I_D - V_{GS}

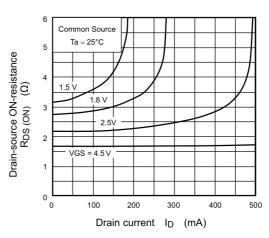


Fig. 7.4 R_{DS(ON)} - I_D

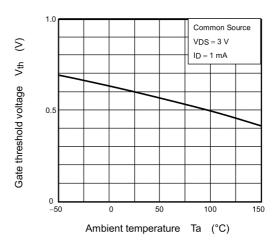


Fig. 7.6 V_{th} - T_a



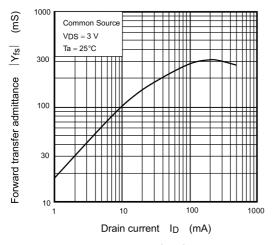


Fig. 7.7 |Y_{fs}| - I_D

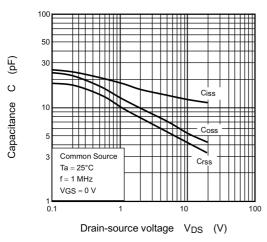


Fig. 7.9 C - V_{DS}

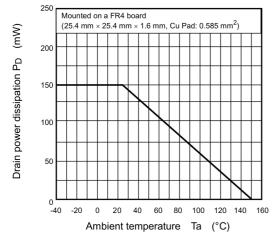


Fig. 7.11 P_D - T_a

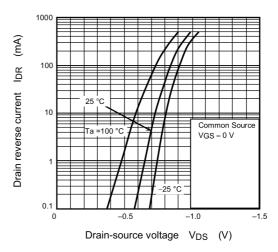


Fig. 7.8 IDR - VDS

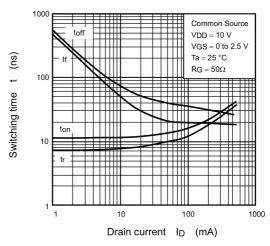


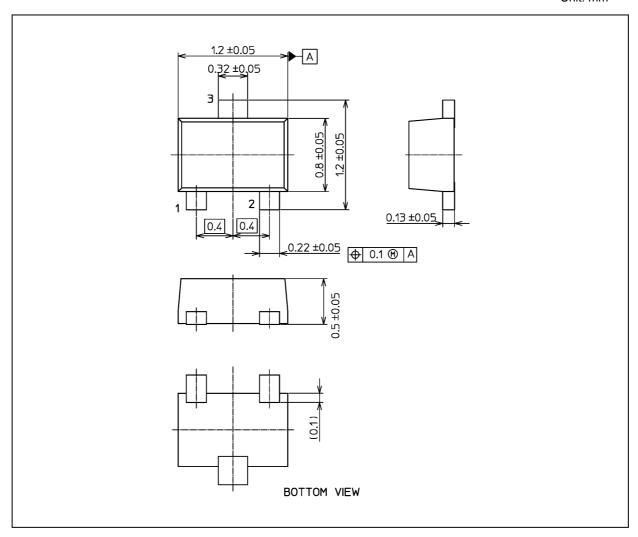
Fig. 7.10 t - I_D

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.5 mg (typ.)

	Package Name(s)
Nickname: VESM	



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